

### General Description

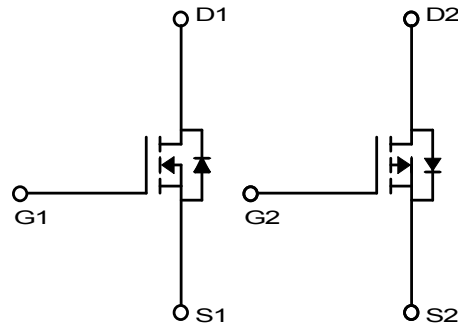
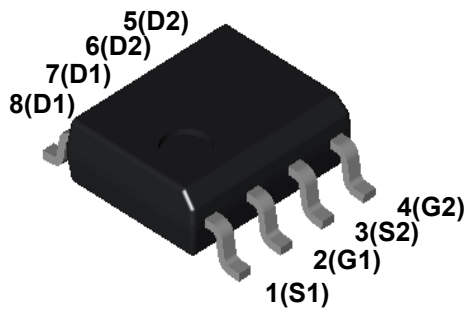
The MDS9651 uses advanced MagnaChip's MOSFET Technology to provide low on-state resistance, high switching performance and excellent reliability

### Features

- |   |  |
|---|--|
| <b>N-Channel</b> <ul style="list-style-type: none"> <li>▫ <math>V_{DS} = 30V</math></li> <li>▫ <math>I_D = 6.9A @ V_{GS} = 10V</math></li> <li>▫ <math>R_{DS(ON)} &lt; 28m\Omega @ V_{GS} = 10V</math></li> <li>▫ <math>R_{DS(ON)} &lt; 42m\Omega @ V_{GS} = 4.5V</math></li> </ul> | <b>P-Channel</b> <ul style="list-style-type: none"> <li><math>V_{DS} = -30V</math></li> <li><math>I_D = -6.0A @ V_{GS} = -10V</math></li> <li><math>R_{DS(ON)} &lt; 35m\Omega @ V_{GS} = -10V</math></li> <li><math>R_{DS(ON)} &lt; 55m\Omega @ V_{GS} = -4.5V</math></li> </ul> |
|---|--|

### Applications

- Inverters
- General purpose applications



### Absolute Maximum Ratings ( $T_a = 25^\circ C$ unless otherwise noted)

Characteristics	Symbol	Rating		Unit	
		N-Ch	P-Ch		
Drain-Source Voltage	$V_{DSS}$	30	-30	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	$\pm 20$	V	
Continuous Drain Current	$I_D$	$T_a = 25^\circ C$	6.9	-6.0	A
		$T_a = 100^\circ C$	4.3	-4.1	A
Pulsed Drain Current	$I_{DM}$	30	-30	A	
Power Dissipation <sup>(1)</sup>	$P_D$	$T_a = 25^\circ C$	2	2	W
		$T_a = 100^\circ C$	0.8	0.8	W
Single Pulse Avalanche Energy <sup>(2)</sup>	$E_{AS}$	18	60.5	mJ	
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~150		$^\circ C$	

### Thermal Characteristics

Characteristics	Device	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient(Steady-State) <sup>(1)</sup>	N-Ch	$R_{\theta JA}$	62.5	$^\circ C/W$
Thermal Resistance, Junction-to-Case	N-Ch	$R_{\theta JC}$	60	
Thermal Resistance, Junction-to-Ambient(Steady-State) <sup>(1)</sup>	P-Ch	$R_{\theta JA}$	62.5	
Thermal Resistance, Junction-to-Case	P-Ch	$R_{\theta JC}$	40	

## Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDS9651URH	-55~150°C	SOIC-8	Tape & Reel	Halogen Free

## N-channel Electrical Characteristics (T<sub>a</sub> = 25°C unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.0	1.9	3.0	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V	-	-	1.0	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	0.1	
Drain-Source ON Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 6.9A	-	21.5	28.0	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.0A	-	31.5	42.0	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 6.9A	-	15.4	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15V, I <sub>D</sub> = 6.9A, V <sub>GS</sub> = 10V	-	6.94	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.54	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.96	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	334	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	48	-	
Output Capacitance	C <sub>oss</sub>		-	83	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>L</sub> = 2.2Ω, R <sub>GEN</sub> = 3Ω	-	3.5	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	25.4	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	14.2	-	
Turn-Off Fall Time	t <sub>f</sub>		-	10.5	-	
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V	-	0.75	1.0	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 6.9A, di/dt = 100A/μs	-	16.5	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	7.8	-	nC

Note :

1. Surface mounted FR-4 board with 2oz. Copper.
2. Starting T<sub>J</sub> = 25°C, L = 1mH, I<sub>AS</sub> = 6A, V<sub>DD</sub> = 15V, V<sub>GS</sub> = 10V

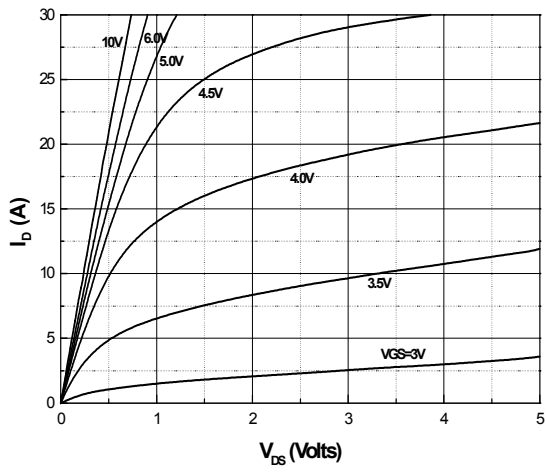
**P-channel Electrical Characteristics (T<sub>a</sub> = 25°C unless otherwise noted)**

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V	-30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-1.9	-3.0	
Drain Cut-Off Current	I <sub>DSS</sub>	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V	-	-	-1.0	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	±0.1	
Drain-Source ON Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -6.0A	-	30.5	35.0	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5.0A	-	41.5	55.0	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -6.0A	-	13	-	S
<b>Dynamic Characteristics</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -6.0A, V <sub>GS</sub> = -10V	-	18.4	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.1	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	3.6	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	874	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	103	-	
Output Capacitance	C <sub>oss</sub>		-	166	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, R <sub>L</sub> = 2.7Ω, R <sub>GEN</sub> = 3Ω	-	9.8	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	29.8	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	26.3	-	
Turn-Off Fall Time	t <sub>f</sub>		-	8.6	-	
<b>Drain-Source Body Diode Characteristics</b>						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	-	-0.75	-1.0	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -6.0A, di/dt = 100A/μs	-	20	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	12.3	-	nC

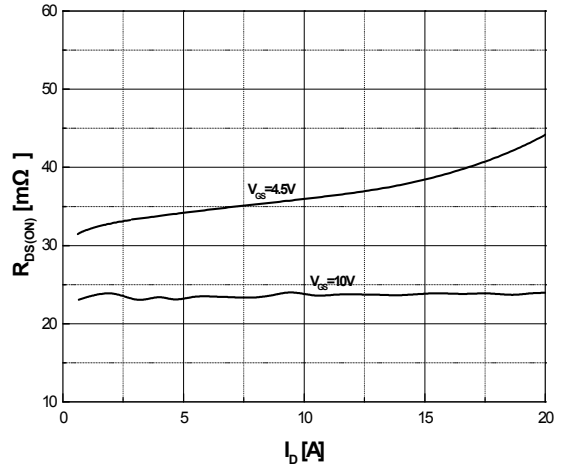
Note :

1. Surface mounted RF4 board with 2oz. Copper.
2. Starting T<sub>J</sub> = 25°C, L = 1mH, I<sub>AS</sub> = -11A, V<sub>DD</sub> = -15V, V<sub>GS</sub> = -10V

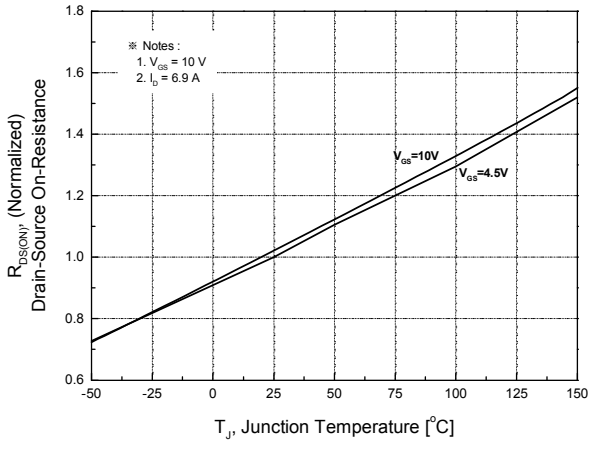
**N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



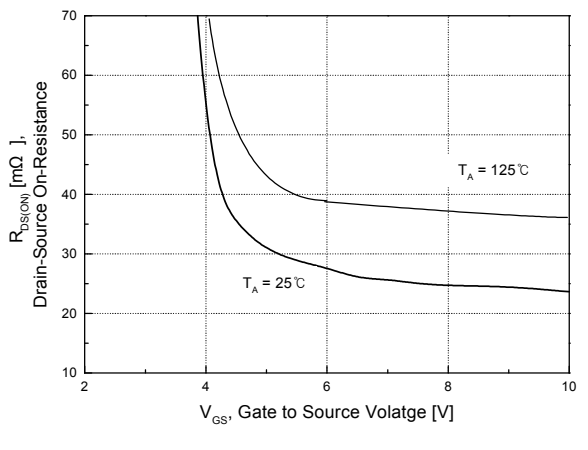
**Fig.1 On-Region Characteristics**



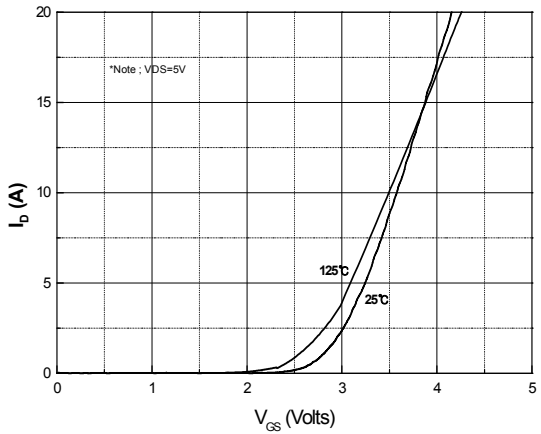
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



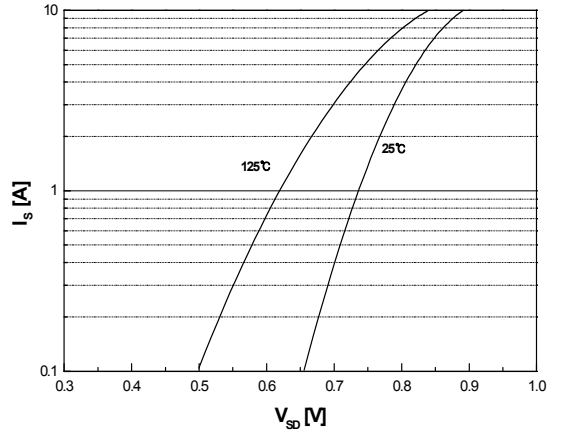
**Fig.3 On-Resistance Variation with Temperature**



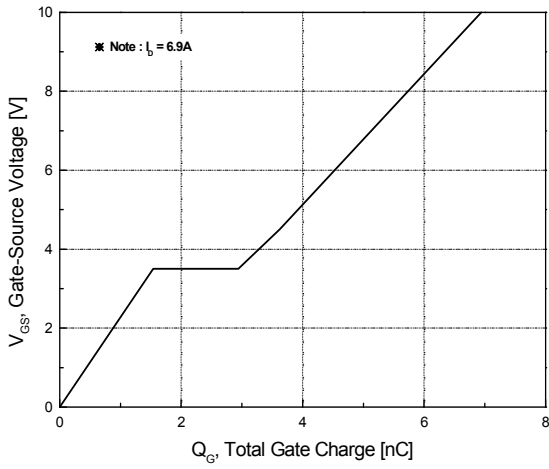
**Fig.4 On-Resistance Variation with Gate to Source Voltage**



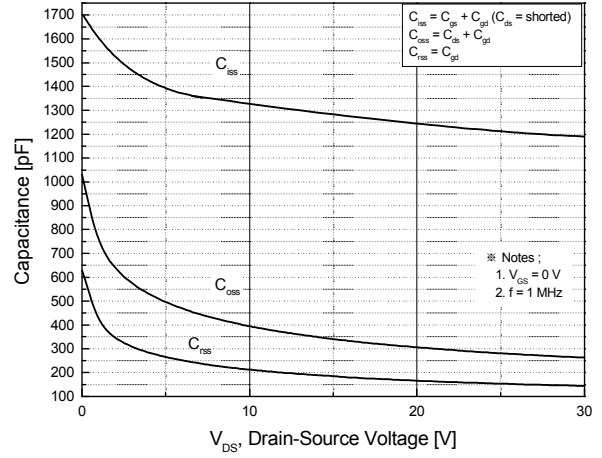
**Fig.5 Transfer Characteristics**



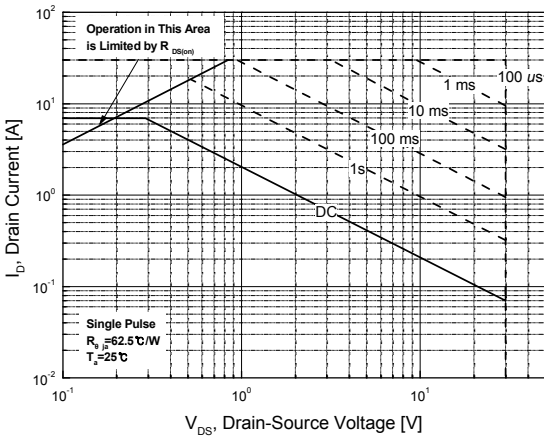
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



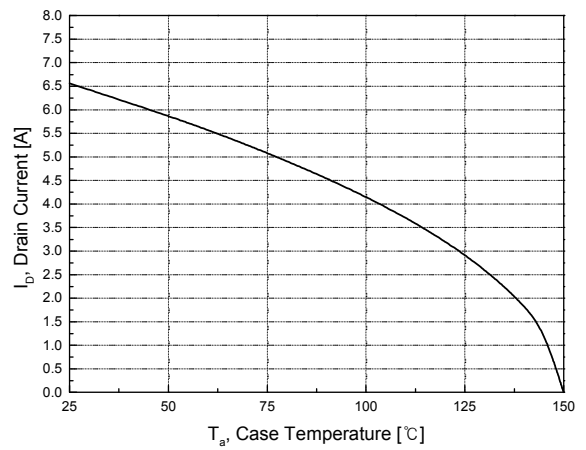
**Fig.7 Gate Charge Characteristics**



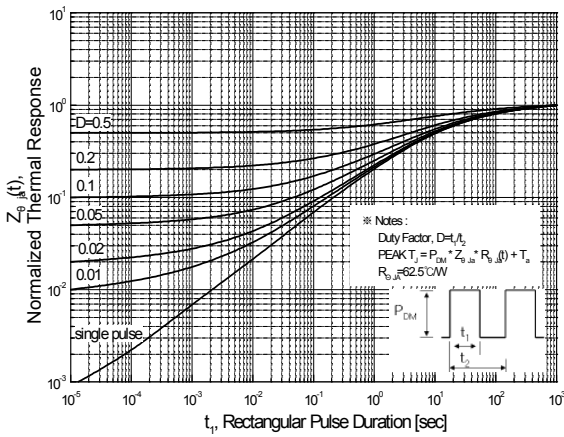
**Fig.8 Capacitance Characteristics**



**Fig.9 Maximum Safe Operating Area**

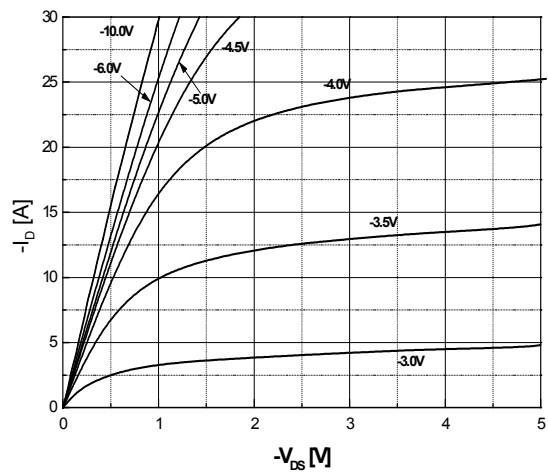


**Fig.10 Maximum Drain Current Vs. Case Temperature**

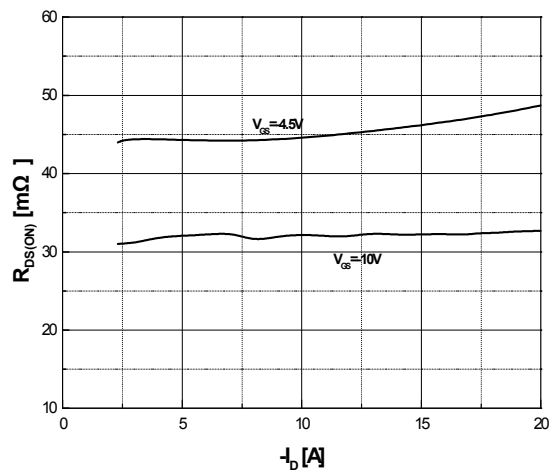


**Fig.11 Transient Thermal Response Curve**

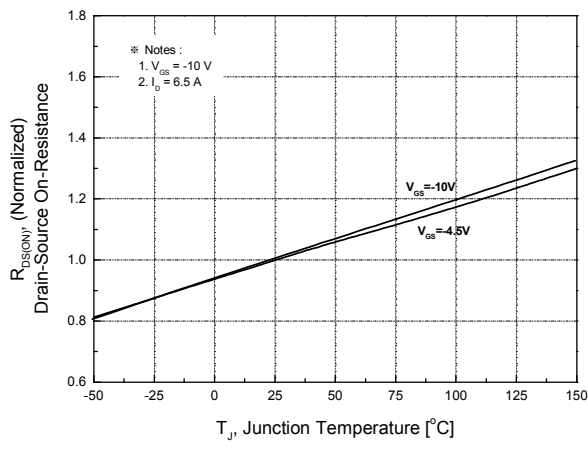
**P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



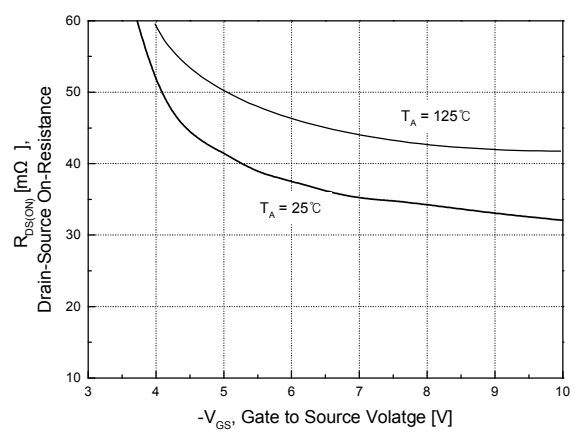
**Fig.1 On-Region Characteristics**



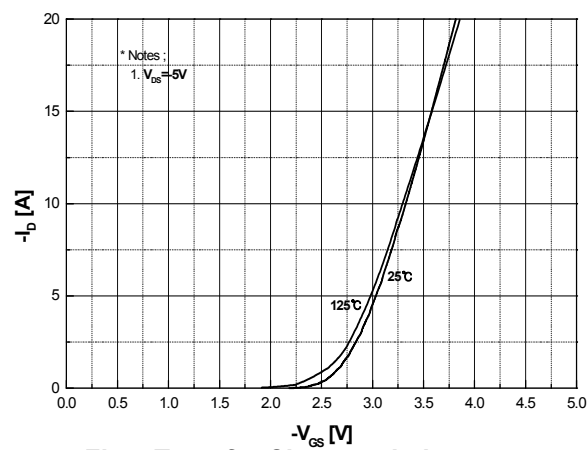
**Fig.2 On-Resistance Variation with Drain Current and Gate Voltage**



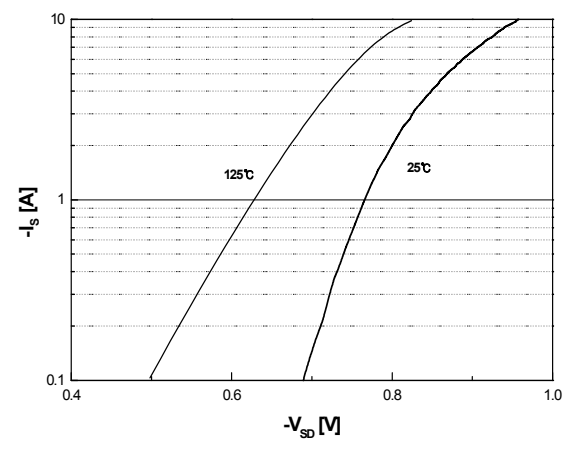
**Fig.3 On-Resistance Variation with Temperature**



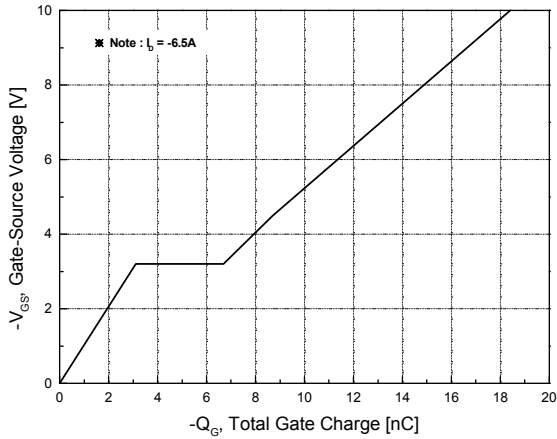
**Fig.4 On-Resistance Variation with Gate to Source Voltage**



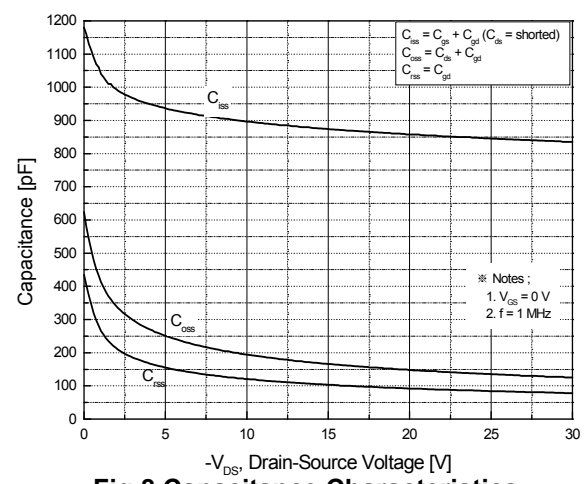
**Fig.5 Transfer Characteristics**



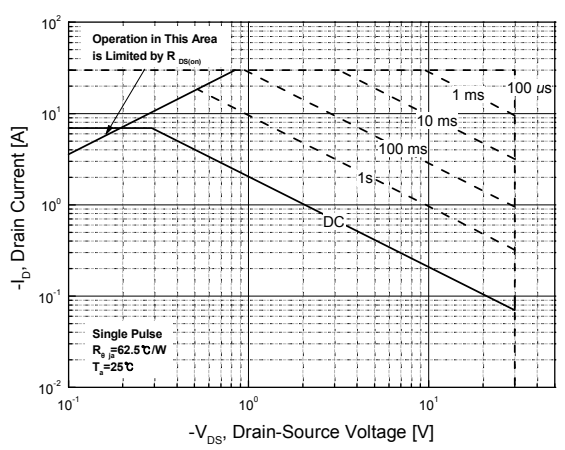
**Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature**



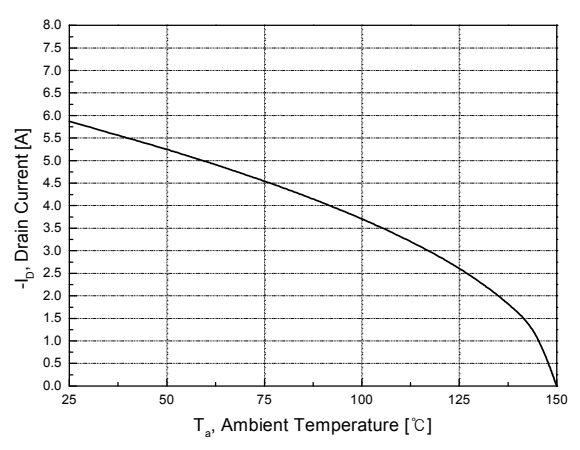
**Fig.7 Gate Charge Characteristics**



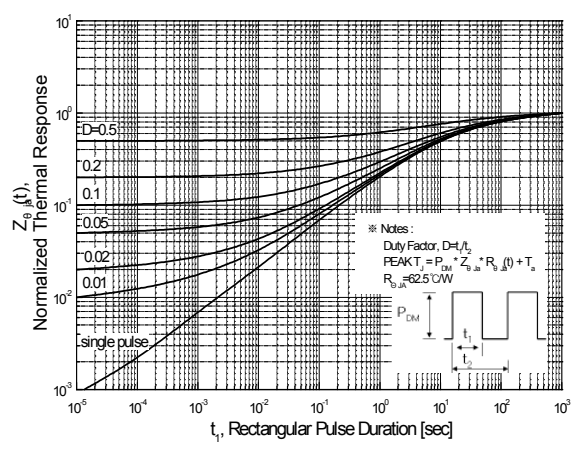
**Fig.8 Capacitance Characteristics**



**Fig.9 Maximum Safe Operating Area**



**Fig.10 Maximum Drain Current vs. Case Temperature**

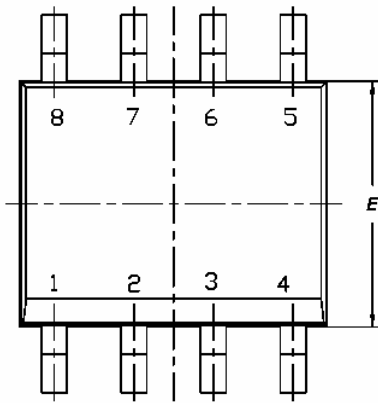


**Fig.11 Transient Thermal Response Curve**

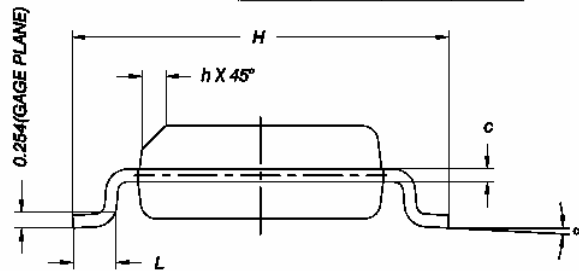
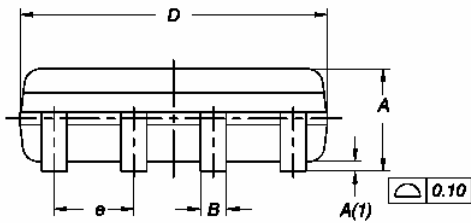
## Physical Dimensions

### 8 Leads SOIC

Dimensions are in millimeters unless otherwise specified



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.35	1.55	1.75
A(1)	0.10	0.175	0.25
B	0.38	0.445	0.51
C	0.19	0.22	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27 BSC		
H	5.80	6.00	6.20
L	0.50	0.715	0.93
$\alpha$	0°	4°	8°
h	0.25	0.375	0.50





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Email : koreasales@magnachip.com

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